

# PBSS4260PANS

60 V, 2 A NPN/NPN low VCEsat (BISS) double transistor
15 December 2015

Product data sheet

## 1. General description

NPN/NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) double transistor in a leadless medium power DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP/PNP complement: PBSS5260PAPS

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Reduced Printed-Circuit Board (PCB) requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- High energy efficiency due to less heat generation
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

### 3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- LED lighting
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	60	V
Ic	collector current			-	-	2	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	3	Α



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	200	mΩ

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	1 2 3 E1	E1 B1 C2
6	C1	collector TR1	Transparent top view  DFN2020D-6 (SOT1118D)	sym140
7	C1	collector TR1	DEN2020D-0 (3011110D)	
8	C2	collector TR2		

## 6. Ordering information

Table 3. Ordering information

Table of Craoming Information						
Type number	Package					
	Name	Description	Version			
PBSS4260PANS	DFN2020D-6	DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118D			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4260PANS	3L

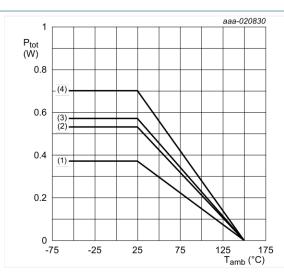
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
$V_{CBO}$	collector-base voltage	open emitter		-	60	V
$V_{CEO}$	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	2	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	3	Α
I <sub>B</sub>	base current			-	0.3	Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
Per device						
$P_{tot}$	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, standard footprint
- (3) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>

Fig. 1. Power derating curves

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	338	K/W
	from junction to ambient		[2]	-	-	219	K/W
ambient	ambient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
Per device							
R <sub>th(j-a)</sub>	thermal resistance		[1]	-	-	246	K/W
	from junction to ambient		[2]	-	-	161	K/W
			[3]	-	-	172	K/W
			[4]	-	-	131	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 Printed-Circuit Board (PCB), 4-layer copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

PBSS4260PANS

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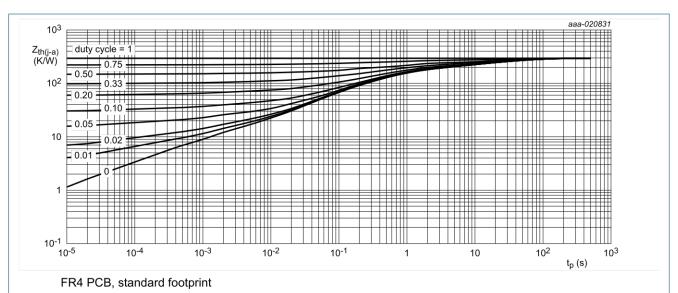
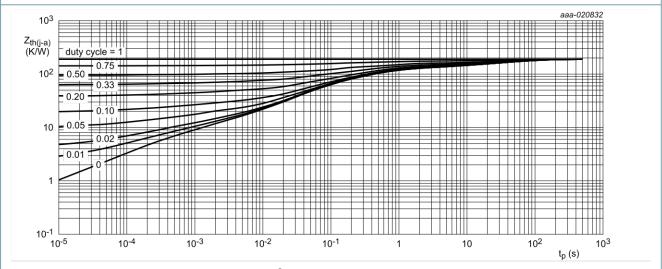
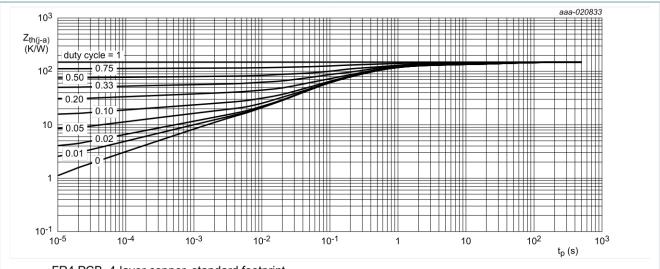


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



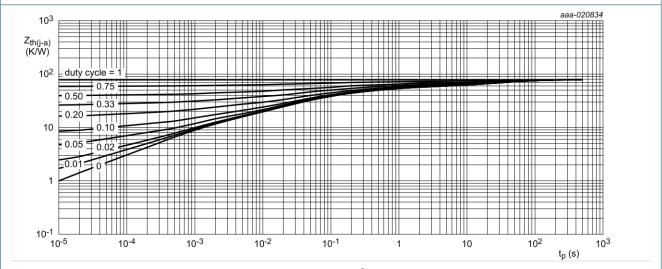
FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, mounting pad for collector 1 cm<sup>2</sup>

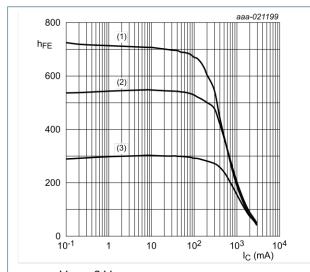
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 48 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
	current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 \text{ V; } I_{C} = 100 \text{ mA; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02; T_{amb} = 25 \text{ °C}$	250	400	-	
		$V_{CE} = 2 \text{ V; } I_{C} = 500 \text{ mA; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	210	330	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	120	190	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$	50	80	-	
02001	collector-emitter saturation voltage	$I_{C}$ = 0.5 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	70	100	mV
		$I_C = 1 \text{ A; } I_B = 50 \text{ mA; pulsed;}$ $t_p \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	140	200	mV
		$I_{C}$ = 2 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	260	350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	200	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C} = 0.5 \text{ A}; I_{B} = 50 \text{ mA}; \text{ pulsed};$ $t_{p} \le 300  \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	0.92	1	V
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	0.96	1.1	V
		$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	1.18	1.3	V
V <sub>BE</sub>	base-emitter voltage	$I_C$ = 0.5 A; $V_{CE}$ = 2 V; pulsed; $t_p \le 300 \ \mu s$ ; $\delta_{factor} \le 0.02$ ; $T_{amb}$ = 25 °C	-	0.77	0.9	V
t <sub>d</sub>	delay time	I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 50 mA; I <sub>Boff</sub> = -50 mA;	-	10	-	ns
t <sub>r</sub>	rise time	T <sub>amb</sub> = 25 °C	-	140	-	ns
t <sub>on</sub>	turn-on time		-	150	-	ns
t <sub>s</sub>	storage time		-	445	-	ns

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>f</sub>	fall time		-	180	-	ns
t <sub>off</sub>	turn-off time		-	625	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	140	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	6.5	-	pF



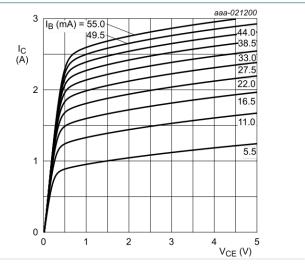


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

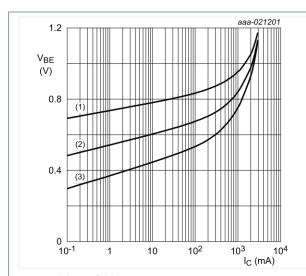
(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 6. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 7. Collector current as a function of collectoremitter voltage; typical values



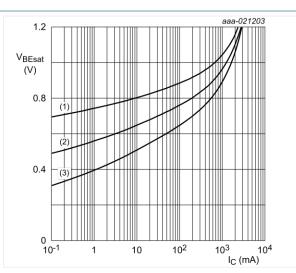
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$





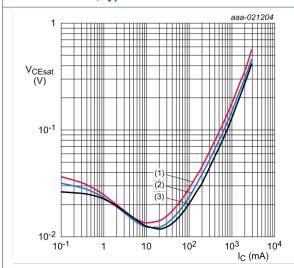
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

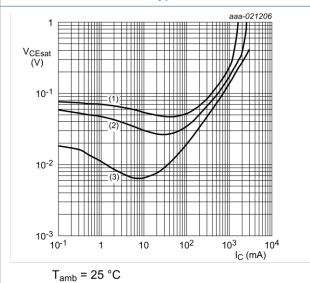


$$I_{\rm C}/I_{\rm B} = 20$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55$$
 °C

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



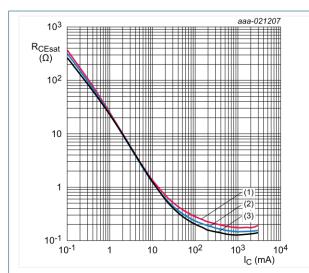
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

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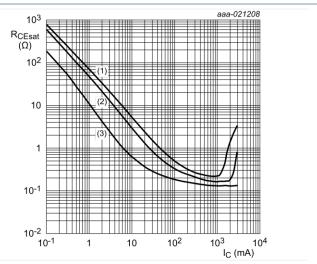


$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

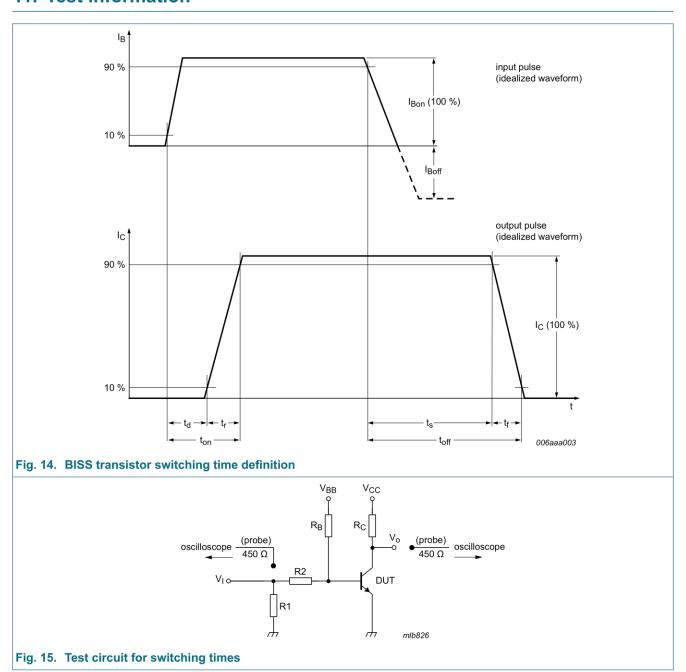
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

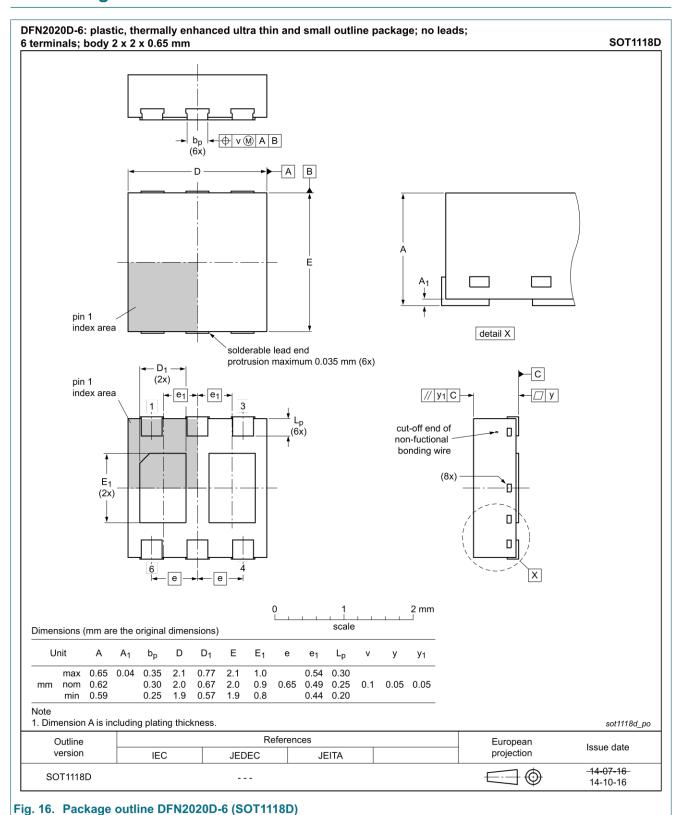
### 11. Test information



### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



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## 13. Soldering

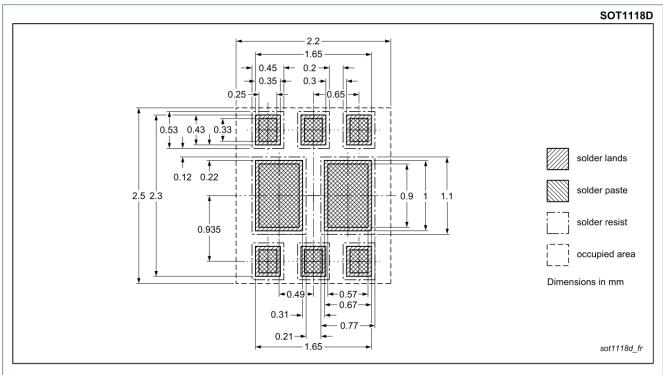


Fig. 17. Reflow soldering footprint for DFN2020D-6 (SOT1118D)

## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4260PANS v.1	20151215	Product data sheet	-	-

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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#### 60 V, 2 A NPN/NPN low VCEsat (BISS) double transistor

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